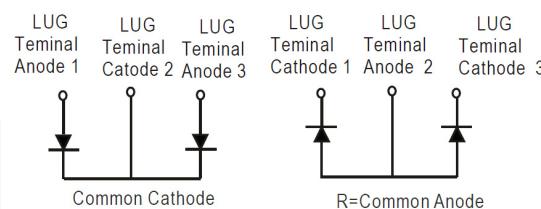


Low V_F Silicon Power Schottky Diode

V_{RRM} = 30 V
I_{F(AV)} = 400 A

Features

- High Surge Capability
- Type 30 V V_{RRM}
- Isolation Type Package
- Electrically Isolated Base Plate
- Not ESD Sensitive

Heavy Three Tower Package


Maximum ratings, at T_j = 25 °C, unless otherwise specified ("R" devices have leads reversed)

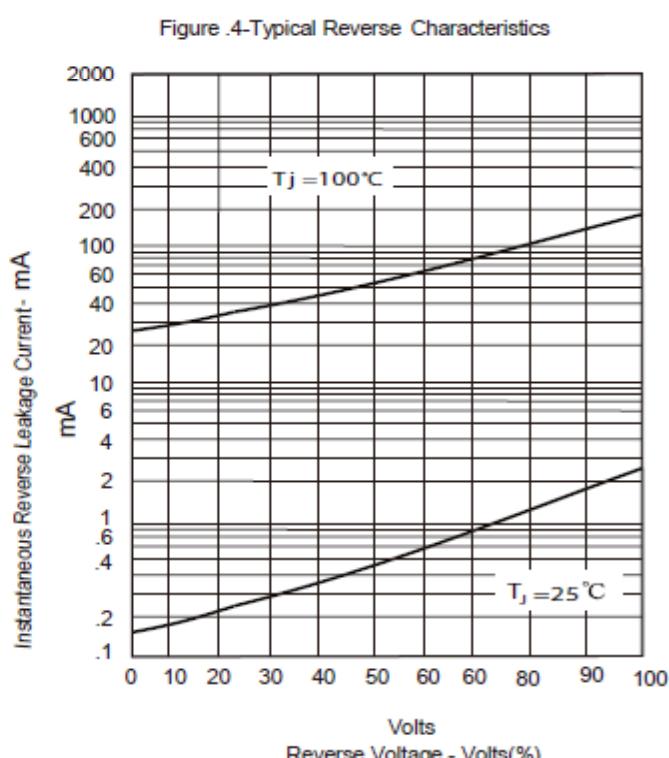
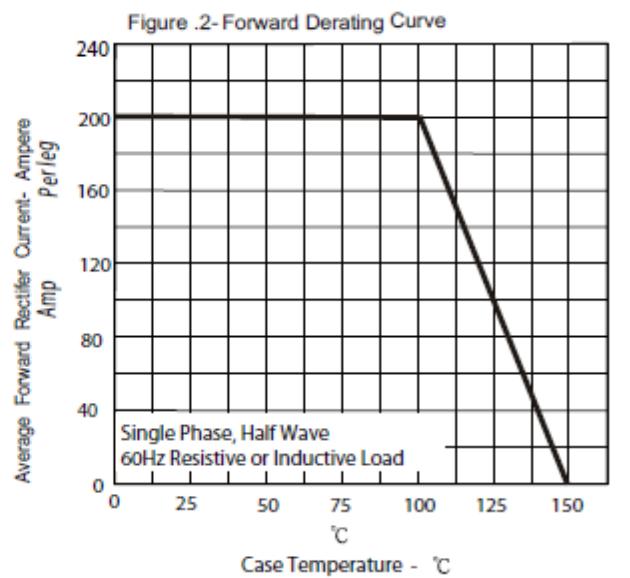
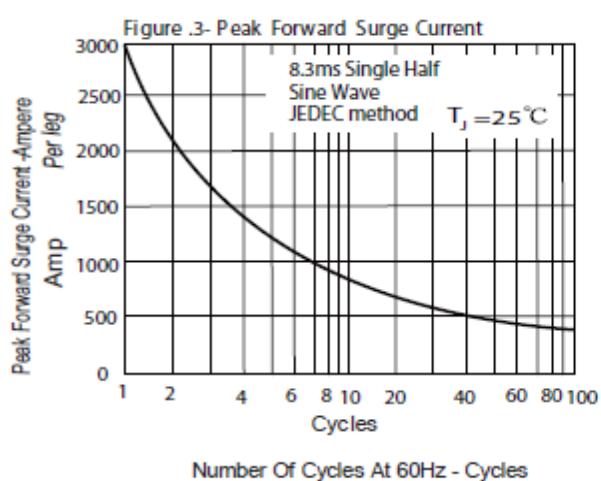
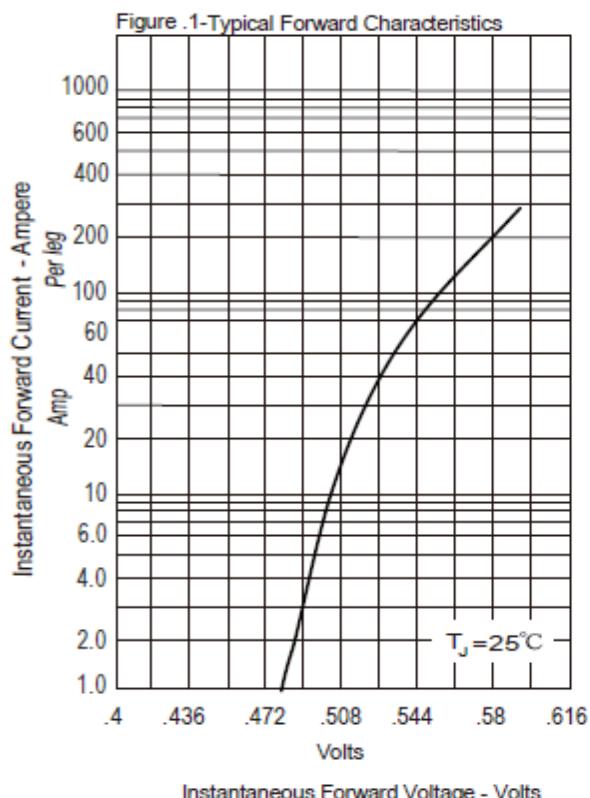
Parameter	Symbol	Conditions	MBRTA40030(R)L	Unit
Maximum recurrent peak reverse voltage	V _{RRM}		30	V
Maximum RMS voltage	V _{RMS}		21	V
Maximum DC blocking voltage	V _{DC}		30	V
Operating temperature	T _j		-55 to 150	°C
Storage temperature	T _{stg}		-55 to 150	°C

Electrical characteristics, at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	MBRTA40030(R)L	Unit
Average forward current (per pkg)	I _{F(AV)}	T _C = 100 °C	400	A
Peak forward surge current (per leg)	I _{FSM}	t _p = 8.3 ms, half sine	3000	A
Maximum instantaneous forward voltage (per leg)	V _F	I _{FM} = 200 A, T _j = 25 °C	0.58	V
Maximum instantaneous reverse current at rated DC blocking voltage (per leg)	I _R	T _j = 25 °C T _j = 100 °C	3 200	mA

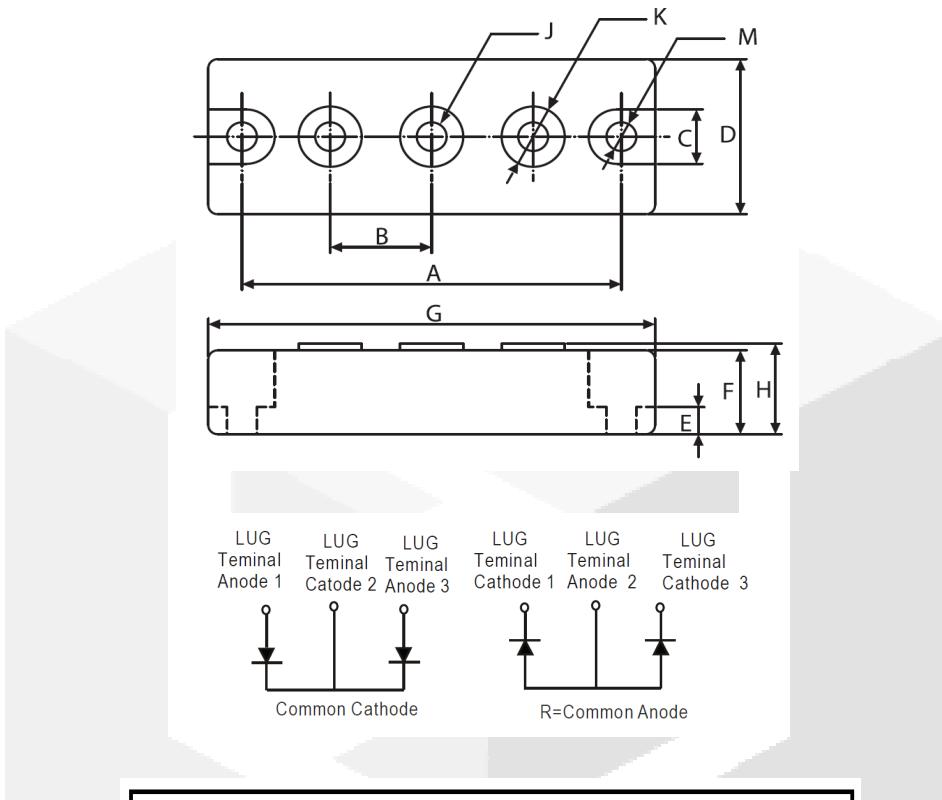
Thermal characteristics

Maximum thermal resistance, junction - case (per leg)	R _{θJC}	0.35	°C/W
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Package dimensions and terminal configuration

Product is marked with part number and terminal configuration.



DIMENSIONS				
	INCHES		MM	
	MIN	MAX	MIN	MAX
A	3.150	NOM	80.01	NOM
B	.872	.892	22.15	22.65
C	.465	.479	11.82	12.18
D	1.337	1.356	33.95	34.45
E	.230	.234	5.84	6.16
F	.725	REF	18.42	REF
G	3.668	3.768	93.17	95.71
H	----	.791	---	20.10
J	1/4 - 20 UNC FULL			
K	.509	.538	12.92	13.68
M	.238	.258	6.05	6.55